

Superconducting gap parameters of MgB_2 obtained on MgB_2/Ag and MgB_2/In junctions

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MgB_2 superconducting wires with critical temperature T_c approaching 40 K were used for preparation of MgB_2/Ag and MgB_2/In junctions. The differential conductance *vs.* voltage characteristics of N-S junctions exhibit clear contribution of Andreev reflection. Using modified BTK theory for s-wave superconductors two order parameters $\Delta_{dirty} \approx 4$ meV and $\Delta_{3D} \approx 2.6$ meV have been determined from temperature dependencies. Surprisingly, larger order parameter Δ_{dirty} vanishes at lower temperature $T_{cdirty} \approx 20$ K than smaller one Δ_{3D} with $T_c \approx 38$ K. Both the magnitudes of the order parameters and their critical temperatures are in good agreement with theoretical calculations of electron-phonon coupling in MgB_2 carried out by Liu et al.

The recent discovery of superconductivity in magnesium diboride¹, with critical temperature T_c about 40K, has raised enormous interest. There appear speculations about potential applications, motivated by the simplicity of the crystal structure of MgB_2 in comparison with the multicomponent high- T_c copper-oxide superconductors. A question arises what are the surface or interface properties of this superconductor in contact with a normal metal, a question extremely important for superconductor electronics. Based on this reason a lot of efforts is made to explain their physical properties. However, normal as well as superconducting parameters of MgB_2 , such as energy gap Δ , Fermi velocity v_F or coherence length ξ has not been exactly determined up to now. Sharoni et al.² measured the value of gap parameters in the range of 5 to 7 meV and suggested that MgB_2 is a conventional BCS s-wave superconductor. Karapetrov et al.³ measured the value of the gap about 5 meV and showed that temperature dependence of the gap follows the BCS form. However, Schmidt et al.⁴ and Kohen and Deutcher⁵ measured value of the gap parameter about 4 meV and Rubbio-Bollinger et al.⁶ about 2 meV only. In all cases, no evidence for the energy gap anisotropy in the tunneling spectra has been observed.

In this letter transport properties of MgB_2/In and MgB_2/Ag contacts are discussed with the aim to contribute to the above mentioned open questions. It is shown that the temperature dependence of the gap parameter with value of 4 meV do not follows BCS form but rather coincides with two-gap model suggested by Liu et al.⁷

MgB_2 superconducting wires were produced by sealing of $150\mu\text{m}$ in diameter straight boron fiber with tungsten core (approximately $15\mu\text{m}$ diameter) and magnesium chips (99.8% pure) into a niobium tube with a component ratio $\text{Mg}:\text{B}=3:1$. The sealed Nb tube was inserted into a quartz tube evacuated to 10 Pa. In order to decrease

the oxygen concentration in the vacuum background the quartz tube was splashed many times with the argon (99.995% pure) before the final filling up with argon (0.3 atm.). Then it was heated slowly up to 970°C with a temperature steps $8^\circ\text{C}/\text{min}$ and kept at this temperature for two hours. The total time of annealing process was four hours. After annealing the quartz tube was removed from the furnace and quenched to room temperature in approximately five minutes. The Nb tube was then removed from the quartz tube and opened to air. MgB_2 wires, originally elastic and straight, were after the above described procedure very brittle.

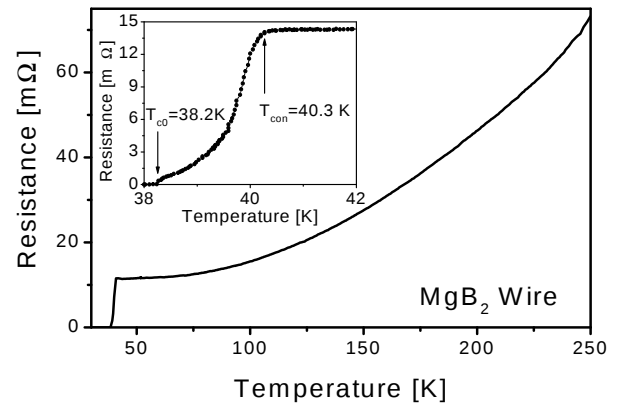


FIG. 1. R-T dependence of the MgB_2 wire.

The junctions using MgB_2 wire were prepared by two methods. To limit fragility, the MgB_2 wire was fixed at four points on the Al_2O_3 substrate by Ag paste. These fixing points were used as contacts for four point measurement of the resistance *vs.* temperature (R-T). Among them the Ag drops were located for completion

of MgB₂/Ag junctions. The differential characteristics were measured between an Ag drop and the MgB₂ wire. The contacts were prepared and measured immediately after the MgB₂ preparation. MgB₂/In junctions were realized by traversing of a freshly cleaved In wire across the MgB₂ wire (MgB₂ wires were kept one day in air atmosphere at room temperature). The resistance of the MgB₂ wire was measured by conventional four point method. The differential characteristics dV/dI vs. V were measured by the low-frequency (800 Hz) phase-sensitive detection technique, using a resistance bridge. The dI/dV vs. V characteristics were obtained by numerical inversion of the measured data. The R-T dependence measured on MgB₂ wire is shown in Fig. 1. This dependence indicates a small inhomogeneity of the wire because the width of the phase transition to superconducting state, ΔT_c , was about 2 K (see the inset in Fig. 1). Typical differential characteristics obtained on MgB₂/Ag and MgB₂/In junctions are shown in Fig. 2 (symbols). These characteristics are typical for N/S junctions (N is normal metal and S is superconductor) with very high transparency of the tunnel barrier.

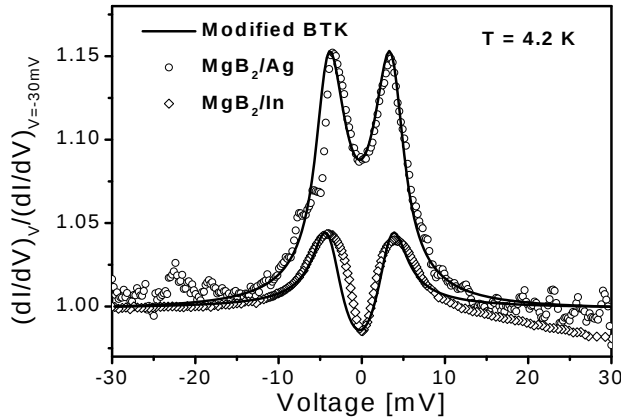


FIG. 2. Differential characteristics dI/dV vs. V measured on MgB₂/Ag and MgB₂/In junctions at temperature T = 4.2 K (symbols - experiments, solid lines - theoretical dependence calculated by modified BTK theory).

Because the contribution of the Andreev reflection to the total junction conductivity is small we suppose the existence of normal metal regions on the MgB₂ surface. Thus the existence of several conducting channels in the junction is possible. But in all cases the superconducting regions are without degraded surface, as indicated by the sharp differential characteristics. Both types of the junctions, shown in Fig. 2, may be well described by the BTK model⁸, where the total current is expressed as:

$$I_{NS} \sim \int_{-\infty}^{\infty} [f(E - eV) - f(E)][1 + A(E) - B(E)]dE,$$

where $f(E)$ is Fermi distribution function, $A(E)$ and $B(E)$ are coefficients giving probability of Andreev and

ordinary reflection, respectively. Due to small discrepancies between the experimental and theoretical curves, for better fitting of experimental curves, we used the modified BTK theory (taking into the finite lifetime of the quasiparticles Γ)⁹. The symbols in the modified BTK theory are as follows: $A = aa^*$, $B = bb^*$, a^* , b^* are the complex conjugate quantities, $a = u_0 v_0 / \gamma$, $b = (u_0^2 - v_0^2)(Z_{eff}^2 + iZ_{eff}) / \gamma$, $\gamma = u_0^2 + (u_0^2 - v_0^2)Z_{eff}^2$, u_0 and v_0 are the Bogoliubov factors given as $u_0^2 = (1 - v_0^2) = \frac{1}{2} \left[1 + \sqrt{(E + i\Gamma)^2 - \Delta^2} / (E + i\Gamma) \right]$, and Z_{eff} is the strength of the barrier. We have fitted the differential characteristics measured on MgB₂/Ag junctions because they were prepared immediately after MgB₂ preparation and we expect small degradation due to the influence of the atmosphere. From fitting of the experimental curves (solid lines in Fig. 2) the maximal value of the gap parameter $\Delta = 4.2$ meV, $Z_{eff} = 0.42$ and $\Gamma = 0.8$ meV were obtained. From the relation¹⁰ $Z_{eff} = (Z^2 + (1 - v_F/v_N)^2 / (4v_F/v_N))^{1/2}$, where v_F and v_N are Fermi velocities of MgB₂ and normal metal, respectively, the Fermi velocity of MgB₂ $v_F = 6.1 \times 10^7$ cms⁻¹ was calculated. From MgB₂/In characteristics the Fermi velocity of MgB₂ $v_F = 4.7 \times 10^7$ cms⁻¹ was obtained. Calculated Fermi velocities of MgB₂ are in reasonable agreement with the band structure calculation of Kortus et al.¹¹ Here we have assumed that there is no artificial or native barrier ($Z=0$).

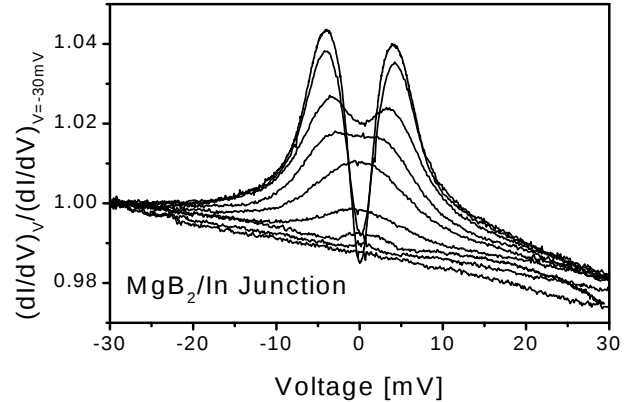


FIG. 3. Temperature dependence of differential characteristics dI/dV vs. V measured on MgB₂/In junctions at temperatures T = 4.2, 8, 13, 18, 24, 28, 34, 37 and 40 K.

Below T_c the low - voltage differential conductance increases with decreasing of temperature (Fig. 3). These curves can be fitted by modified BTK theory. The temperature dependence of the gap parameter (taking into account one energy gap) is shown in Fig. 4 (open circles). Comparison of the gap parameter obtained from experimental curves with the BCS dependence (solid line 1 in Fig. 4) shows large discrepancy. In addition, to fit experimental curves one should change the fitting parameters Z and Γ with temperature. Also the ratio $2\Delta(0)/k_B T_c$

is surprisingly small. For $\Delta(0) = 4$ meV and $T_c = 38$ K (from MgB_2/In junction) we obtained $2\Delta(0)/k_B T_c = 2.4$. A similar value was obtained by tunneling spectroscopy by Kohen and Deutscher in Ref. 5. These authors ascribed a small value of $2\Delta(0)/k_B T_c$ to the existence of superconducting phase with reduced critical temperature T_c at MgB_2/Au interface. However, from our spectra it is clear (see Fig. 3 and Fig. 4) that Andreev reflection disappears at the critical temperature $T_c \approx 38$ K of the bulk material. On the other hand there is deviation of the temperature dependence of the energy gap from the BCS behavior at temperature $T \approx 20$ K. From the temperature dependence of energy gap determined within one-gap model (Fig. 4) one can see two characteristic values of energy gap (≈ 4 meV and ≈ 2.6 meV) and two temperatures (≈ 20 K and ≈ 38 K).

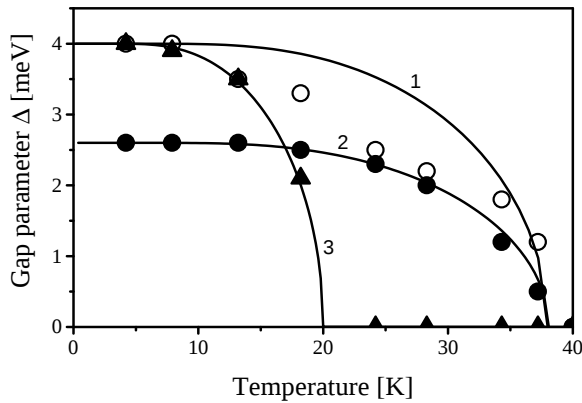


FIG. 4. Temperature dependence of gap parameters in one gap approximation (open circles) and within multigap scenario in dirty (solid triangles) and clean limits (solid circles) obtained from experimental curves shown in Fig. 3. The solid lines 1, 2 and 3 corresponds to BCS relation $\Delta(T)/\Delta(0) = \tanh(\Delta(T)T_c/\Delta(0)T)$

These values correspond to those calculated by Liu *et al.*⁷ within two-gap scenario. They argue that there are two different order parameters in MgB_2 corresponding to two sets of bands. One set of bands is quasi-2D with larger 2D gap while 3D band exhibits 3D gap which is three times smaller in magnitude. From a geometry of our tunnel junctions a tunneling in direction perpendicular to B layers is expected i.e. the tunneling spectra reflect 3D gap namely. On the other hand our samples are not ideal. The large value of smearing parameter Γ indicates dirty regions in contact area. An enhanced defect scattering in dirty regions leads to an averaging of both order parameters that results to an isotropic order parameter and reduced T_c .⁷ Thus our junction can be considered as a parallel connection of two junctions corresponding to the tunneling into the dirty and clean regions respectively. We have fitted the differential characteristics according to above model and we have obtained a good agreement between experimental and the-

oretical curves. The fitting procedure gives for dirty limit $\Delta_{dirty} \approx 4$ meV, $T_{dirty} \approx 20$ K and for clean limit $\Delta_{3D} \approx 4$ meV, $T_c \approx 38$ K. Within this model the fitting parameters Z and Γ were constant in the whole temperature range. Temperature dependences of order parameters Δ_{dirty} and Δ_{3D} are given in Fig. 4. Above values of the order parameters coincide with those calculated in Ref. 7. In order to measure also larger 2D order parameter, tunnel junctions should be prepared in direction parallel to B layers. Such junctions cannot be prepared by technology presented here but can be perhaps formed on MgB_2 epitaxial thin films. The work is in progress. Nevertheless there are already experimental results that give some evidence on existence of the large value of order parameter. Very recently Sharoni *et al.*² measured the maximal value of order parameter ≈ 7 meV by STM/STS which can be ascribed to Δ_{2D} .

In conclusion, we have presented properties of the MgB_2/Ag and MgB_2/In junctions and an analysis of the measured differential characteristics. Our experimental data give an evidence on multigap scenario in MgB_2 . From the fitting procedure the values of $\Delta_{dirty} \approx 4$ meV, $T_{dirty} \approx 20$ K and $\Delta_{3D} \approx 2.6$ meV, $T_c \approx 38$ K, as well as an upper limit of the Fermi velocity $v_F = 6.1 \times 10^7$ cm/s were determined.

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